

TOSHIBA Transistor Silicon PNP Epitaxial Type (PCT process)

2SA1204

Audio Frequency Amplifier Applications

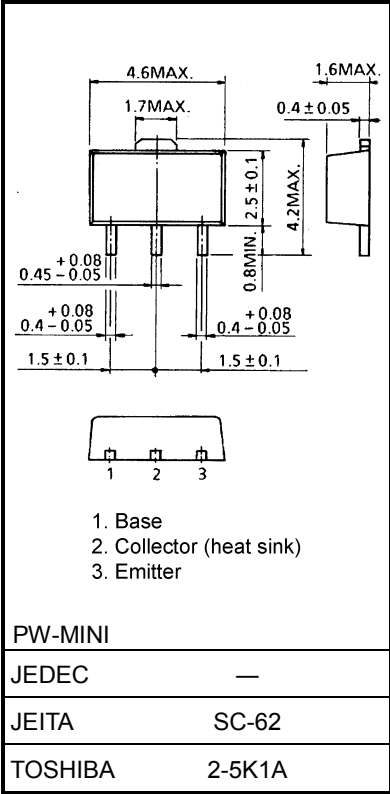
- High DC current gain: $h_{FE} = 100$ to 320
- Suitable for output stage of 1 watts amplifier
- Small flat package
- $P_C = 1.0$ to 2.0 W (mounted on ceramic substrate)
- Complementary to 2SC2884

Maximum Ratings ($T_a = 25^{\circ}\text{C}$)

Characteristics	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	-35	V
Collector-emitter voltage	V_{CEO}	-30	V
Emitter-base voltage	V_{EBO}	-5	V
Collector current	I_C	-800	mA
Base current	I_B	-160	mA
Collector power dissipation	P_C	500	mW
	P_C (Note 1)	1000	
Junction temperature	T_j	150	$^{\circ}\text{C}$
Storage temperature range	T_{stg}	-55 to 150	$^{\circ}\text{C}$

Note 1: Mounted on ceramic substrate ($250\text{ mm}^2 \times 0.8\text{ t}$)

Unit: mm

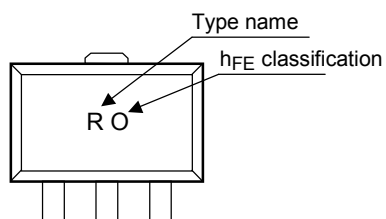


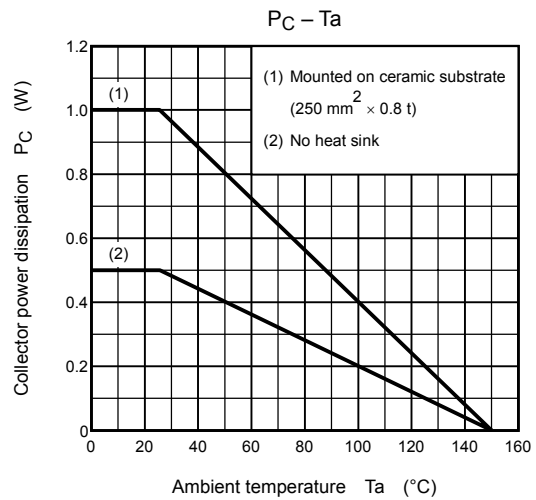
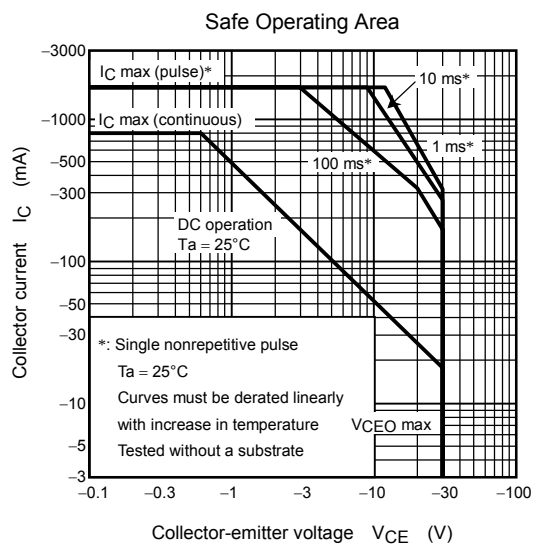
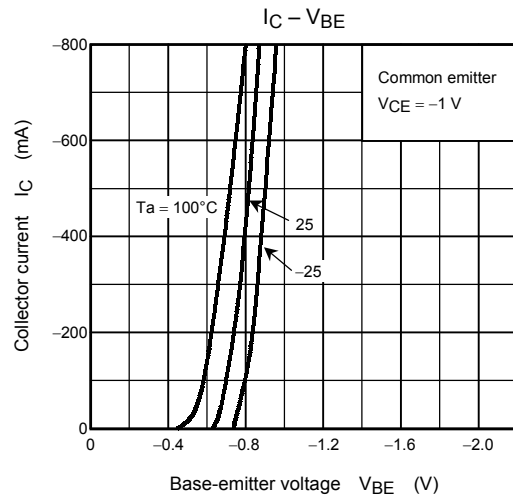
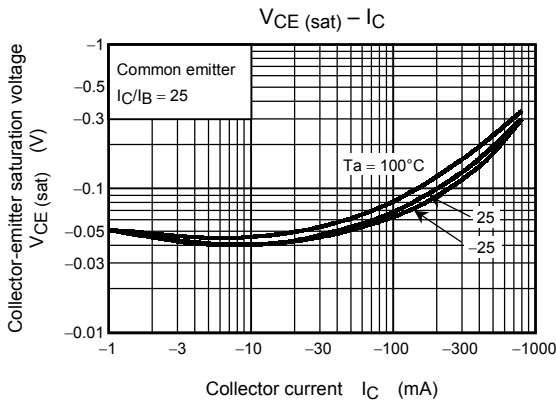
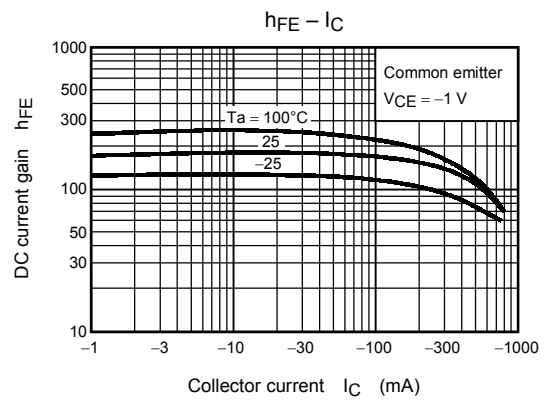
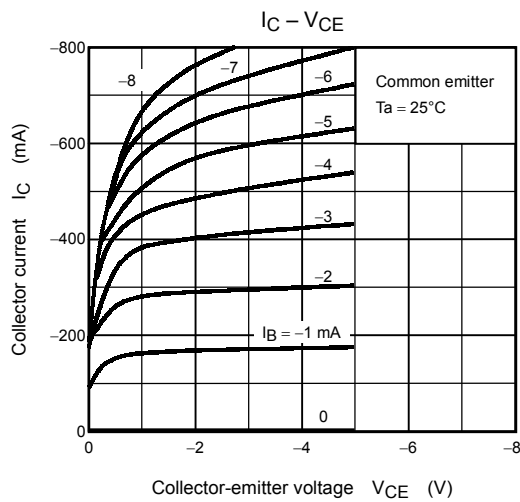
Weight: 0.05 g (typ.)

Electrical Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current	I_{CBO}	$V_{CB} = -35\text{ V}, I_E = 0$	—	—	-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -5\text{ V}, I_C = 0$	—	—	-0.1	μA
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -10\text{ mA}, I_B = 0$	-30	—	—	V
DC current gain	$h_{FE(1)}$ (Note 2)	$V_{CE} = -1\text{ V}, I_C = -100\text{ mA}$	100	—	320	
	$h_{FE(2)}$	$V_{CE} = -1\text{ V}, I_C = -700\text{ mA}$	35	—	—	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -500\text{ mA}, I_B = -20\text{ mA}$	—	—	-0.7	V
Base-emitter voltage	V_{BE}	$V_{CE} = -1\text{ V}, I_C = -10\text{ mA}$	-0.5	—	-0.8	V
Transition frequency	f_T	$V_{CE} = -5\text{ V}, I_C = -10\text{ mA}$	—	120	—	MHz
Collector output capacitance	C_{ob}	$V_{CB} = -10\text{ V}, I_E = 0, f = 1\text{ MHz}$	—	19	—	pF

Note 2: $h_{FE(1)}$ classification O: 100 to 200, Y: 160 to 320

Marking




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